



Document No.: 61352-043

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
	:	
Takeshi TAKAGI	:	Confirmation Number: 1584
	:	
Serial No.: 10/657,799	:	Group Art Unit: 2811
	:	
Filed: September 09, 2003	:	Examiner: Unknown
	:	
For: SEMICONDUCTOR DEVICE	:	

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop IDS  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The relevance of Japanese Patent Laid-Open Gazette No. 2001-210831 is discussed in the present specification.

10/657,799

The rest of the non-English language references were first cited in a corresponding foreign application search report or office action and its relevance discussed therein. A copy of the foreign search report or office action, together with an English language version thereof, is attached for the Examiner's information.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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SHEET 1 OF 1

INFORMATION DISCLOSURE  
CITATION IN AN  
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.  
**61352-043**SERIAL NO.  
**10/657,799**APPLICANT  
**Takeshi TAKAGI**FILING DATE  
**September 09, 2003**GROUP  
**2811**

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US 6,040,610	03/21/2000	Noguchi et al.	
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## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number 4 - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP P2001-210831A	08/03/2001	MATSUSHITA ELECTRIC IND CO LTD		(Japan w/English Abstract)	
		EP 1 102 327 A2	05/23/2001	MATSUSHITA ELECTRIC INDUSTRIAL CO., LTD		X	
		EP 0 921 575 A2	06/09/1999	MATSUSHITA ELECTRIC INDUSTRIAL CO., LTD.		X	

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		TAKAGI A. et al., "A Novel High Performance SiGe Channel Heterostructure Dynamic Threshold pMOSFET (HDTMOS)", IEEE ELECTRON DEVICE LETTERS, 2001. May, Vol.22, No.5, pages 206-208, full text
		TAKAMIYA M. et al., "High Drive-Current Electrically Induced Body Dynamic Threshold SOI MOSFET (EIB-DTMOS) with Large Body Effect and Low Threshold Voltage", IEEE TRANSACTIONS ON ELECTRON DEVICES, 2001. August, Vol.48, No.8, pages 1633 to 1640, full text

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.